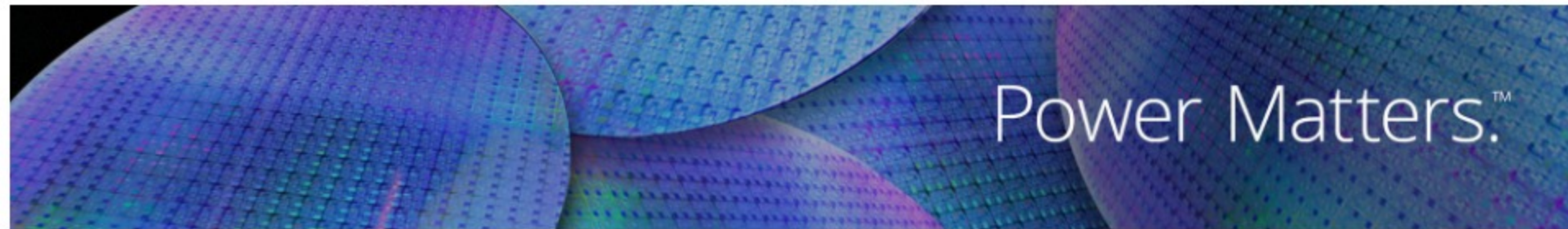


POWER DISCRETES & MODULES

- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ▶ IGBT
- ▶ Power MOSFET
- ▶ Power Modules
- ▶ JFET
- ▶ BJT (BiPolar Junction Transistor)
- ▶ Legacy Power Discrettes & Modules
- ▶ Diode and Rectifier Devices
- ▶ Silicon Carbide (SiC) Semiconductor
  - ▶ SiC Modules
  - **SiC Schottky Barrier Diodes**
  - SiC MOSFET



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MSC010SDA170B

Product Status

■ In Production

Overview Applications Resources Diagrams Ordering Support

The silicon carbide (SiC) power Schottky barrier diodes (SBD) product line from Microsemi increases your performance over silicon diode solutions while lowering your total cost of ownership for high voltage applications. The MSC010SDA170B is a 1700 V, 10 A SiC SBD in a two-lead TO-247 package.



Package Carrier: Tube

Electrical Rating	Symbol	Min	Typ	Max	Unit
Forward Voltage (V)	V <sub>F</sub>		1.5	1.8	V
Environmental Rating	Symbol	Min	Typ	Max	Unit
Junction Temperature (°C)	T <sub>J</sub>	-55		175	°C
Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Forward Current (A)	I <sub>F</sub>			10	A
Reverse Breakdown Voltage	V <sub>BR</sub>			1700	V

This part can be found in the following product categories:

- Power Discrettes & Modules ▶ Silicon Carbide (SiC) Semiconductor
- Power Discrettes & Modules ▶ Silicon Carbide (SiC) Semiconductor ▶ SiC Schottky Barrier Diodes